

# Radiation Testing of Versatile Transceiver for Versatile Link Project

*Results and plans*

*Sarah Seif El Nasr-Storey*

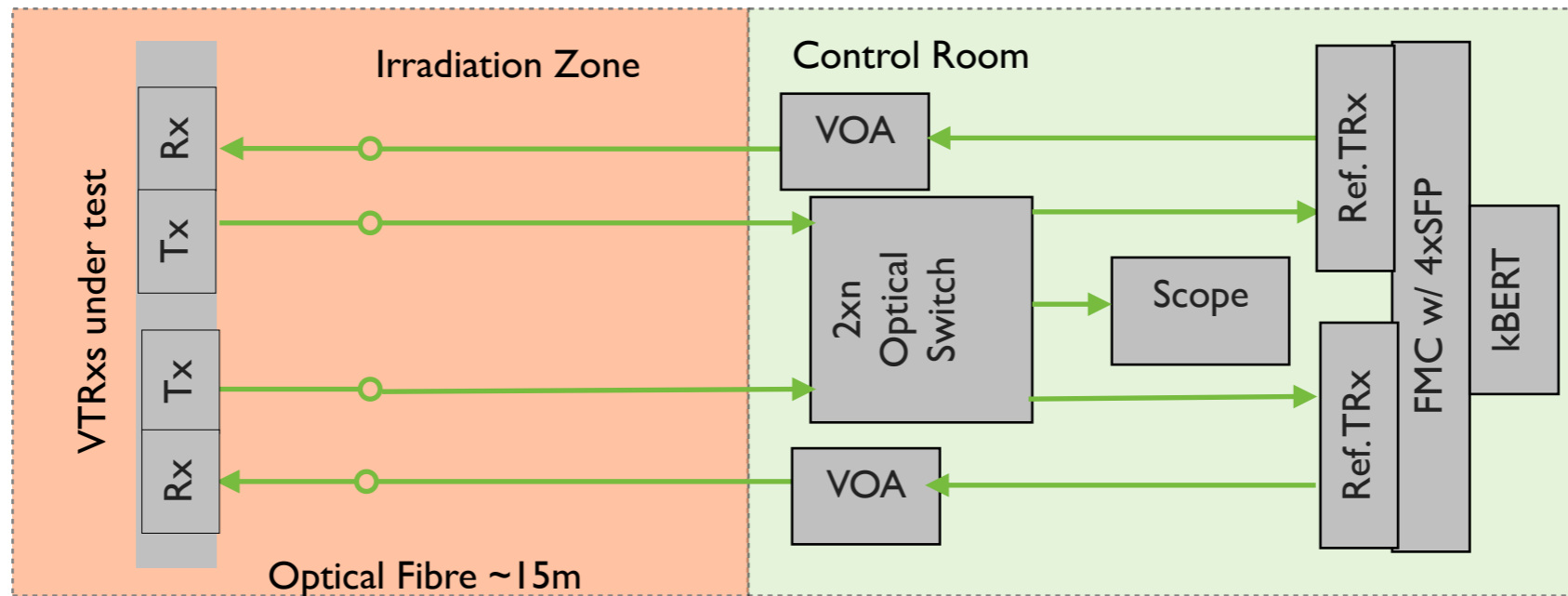
*Opto Working Group Mini Workshop*

*CERN, 21st March 2014*



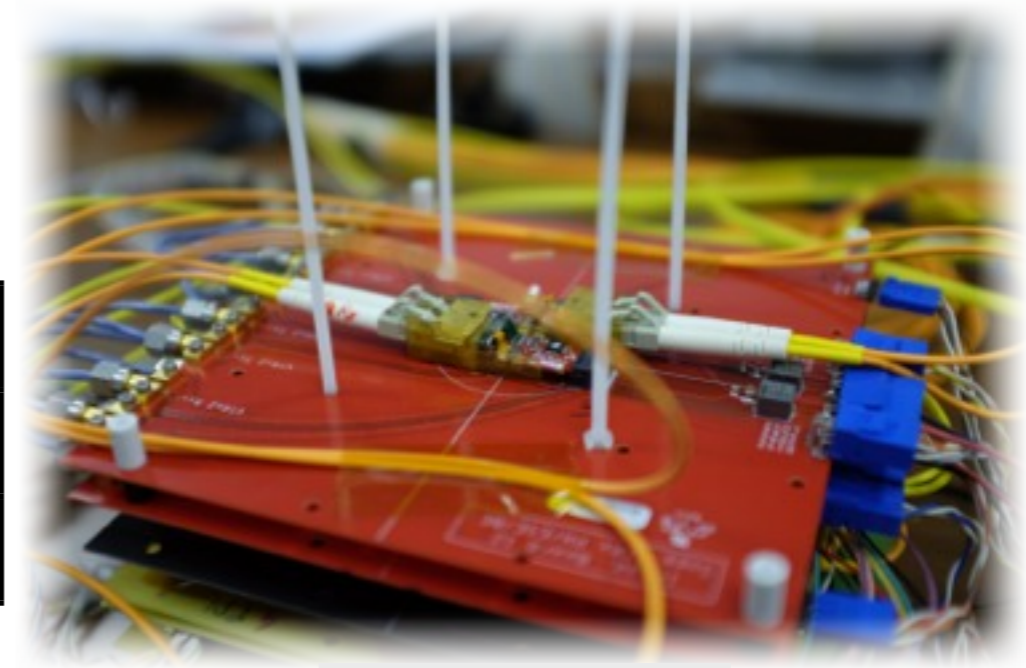
- Introduction
- Results from radiation test
- Conclusions

- First radiation test of complete Versatile Transceiver
  - 20 MeV neutron beam in Louvain-La-Neuve , total dose of  $\sim 1 \times 10^{15}$  n/cm<sup>2</sup>



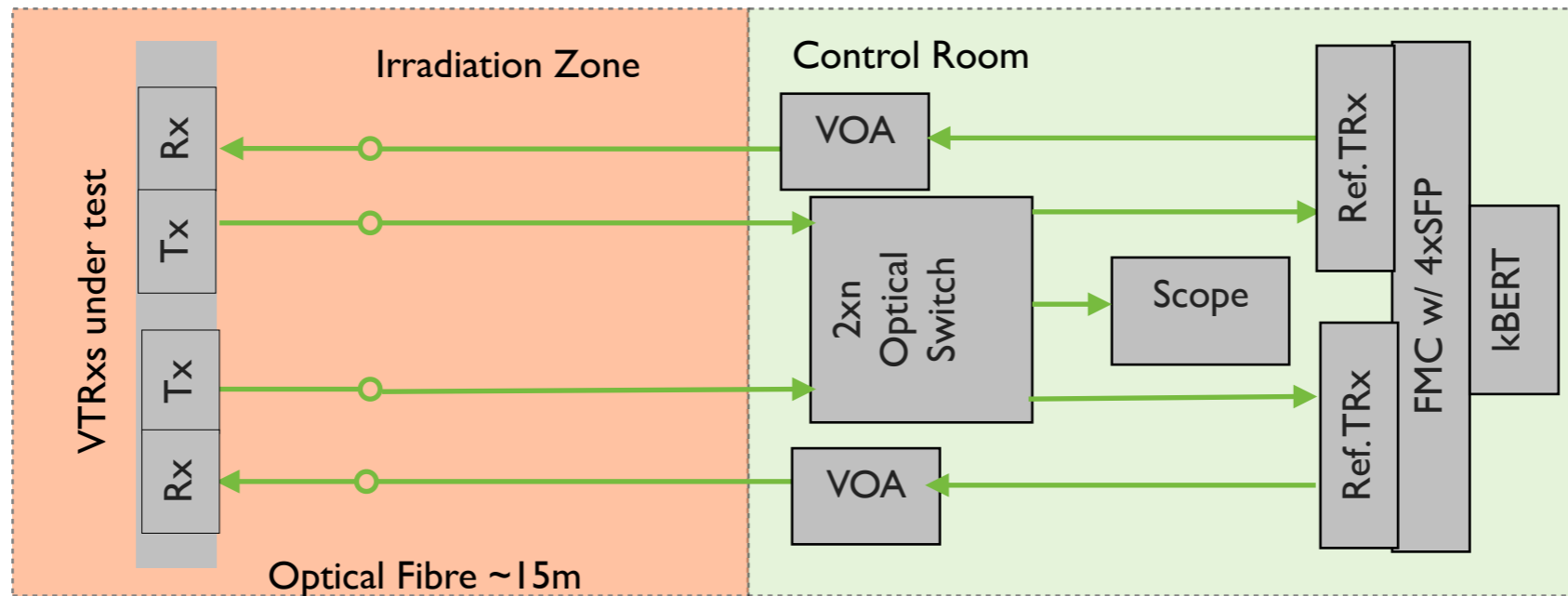
DUTs	Tx	ROSA	# Tested
SMVTRx	1310 nm EEL	InGaAs	2
MMVTRx	850 nm VCSEL	GaAs	2

*Devices irradiated in UCL November 2013*



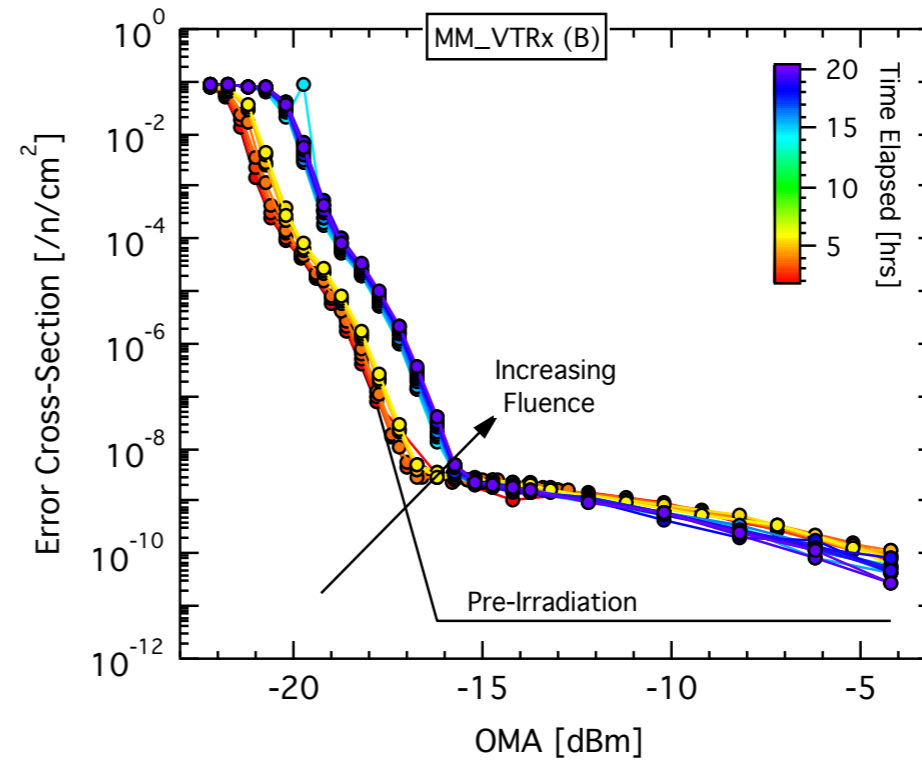
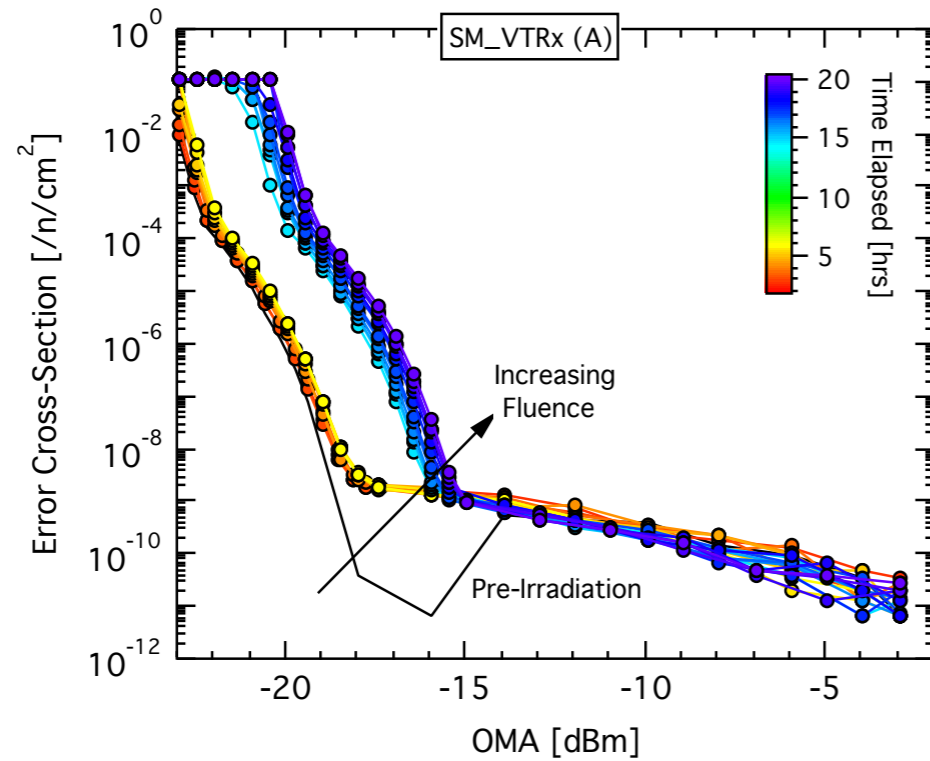
*VTRx on irradiation PCB*

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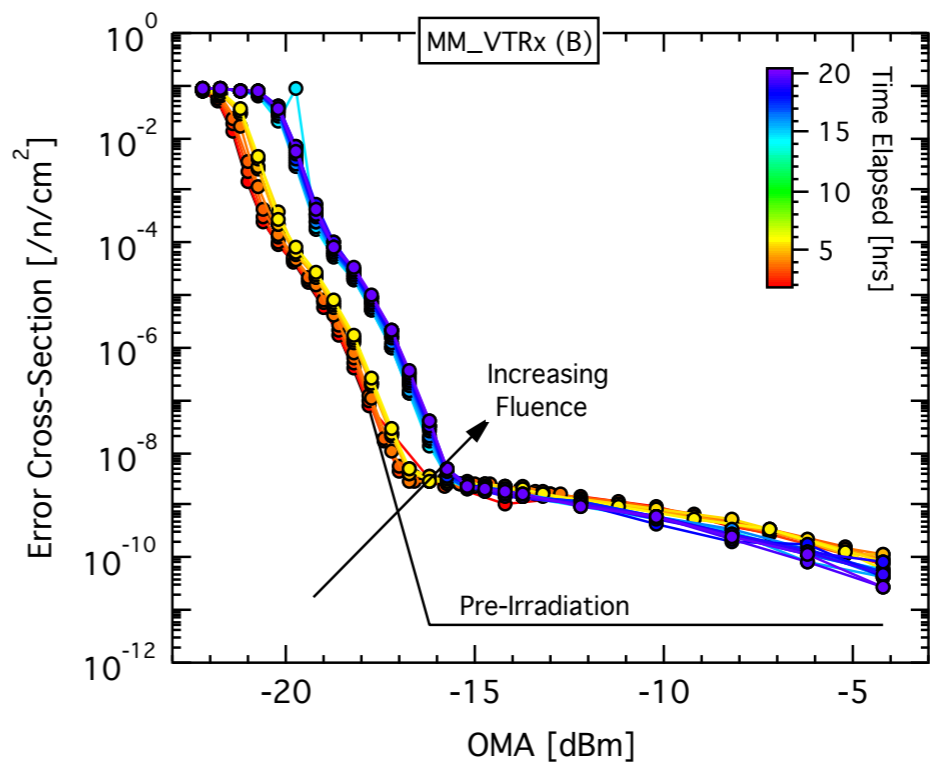
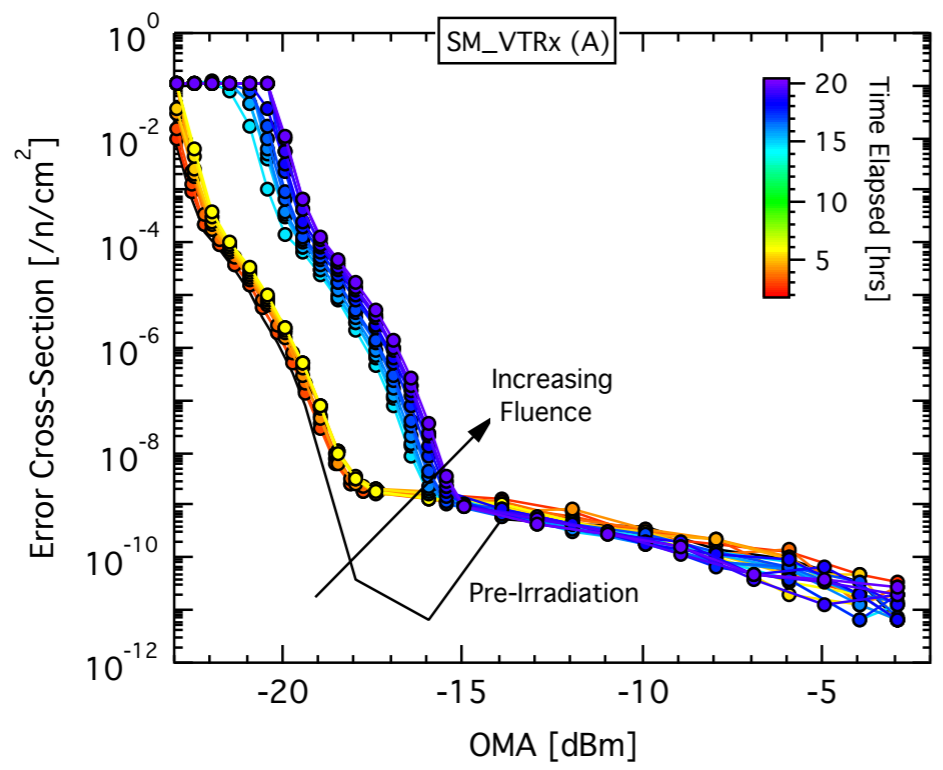


VTRx Component under test	On-line Measurement
ROSA	Sensitivity to SEUs
ROSA	Responsivity
ROSA	Leakage Current
TOSA	Threshold Current
TOSA	Slope Efficiency
TOSA	Transmitted Eye
GBLD	SEUs

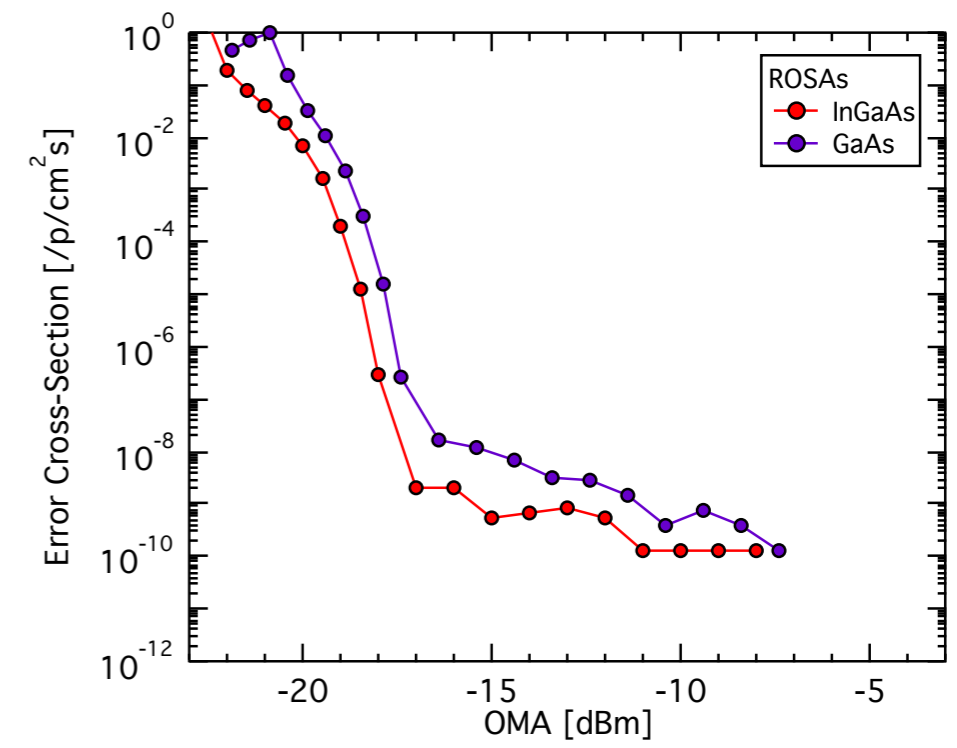
- Sensitivity of VTRx to SEUs ( on receiver side ) measured during the test
  - Expected increase in BER during irradiation because of SEUs



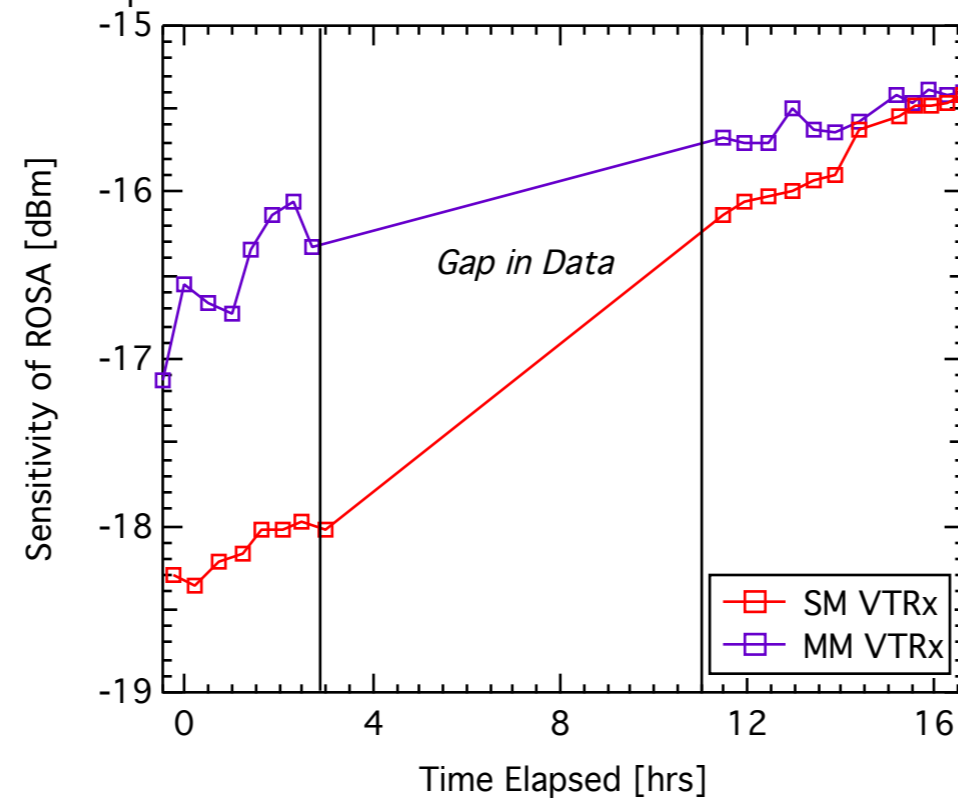
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- Error cross-section comparable with other test results
  - same ROSAs tested in PSI proton beam-line

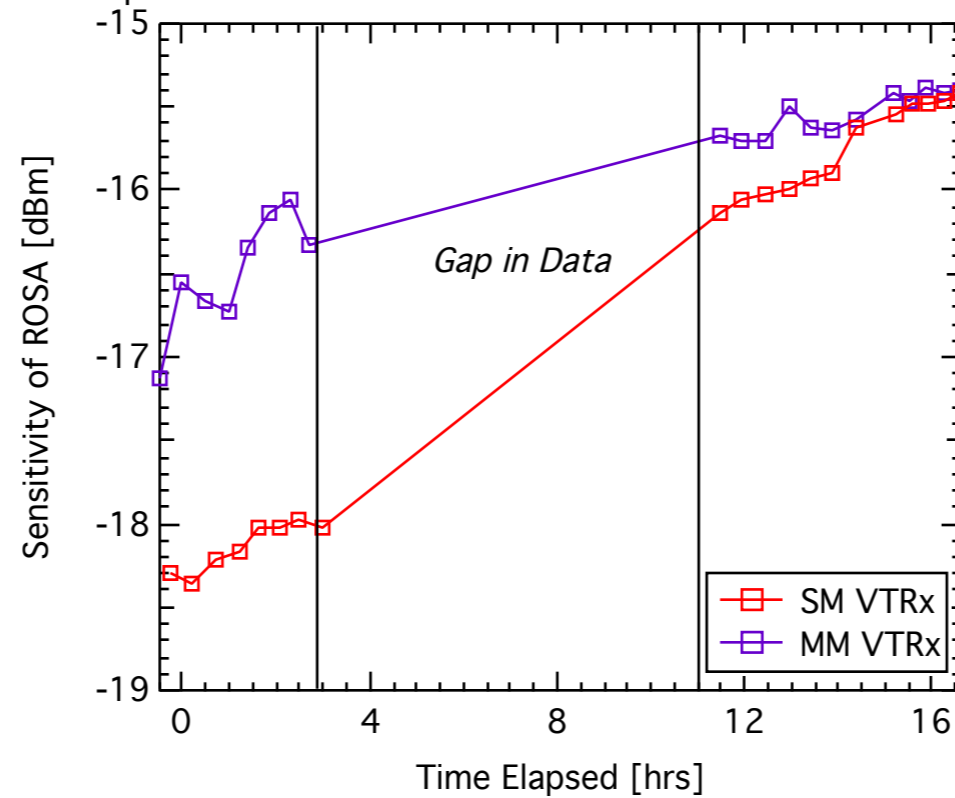


- Sensitivity of VTRx ROSAs to SEUs changes during the irradiation
  - bigger change in SM VTRx compared to MM VTRx



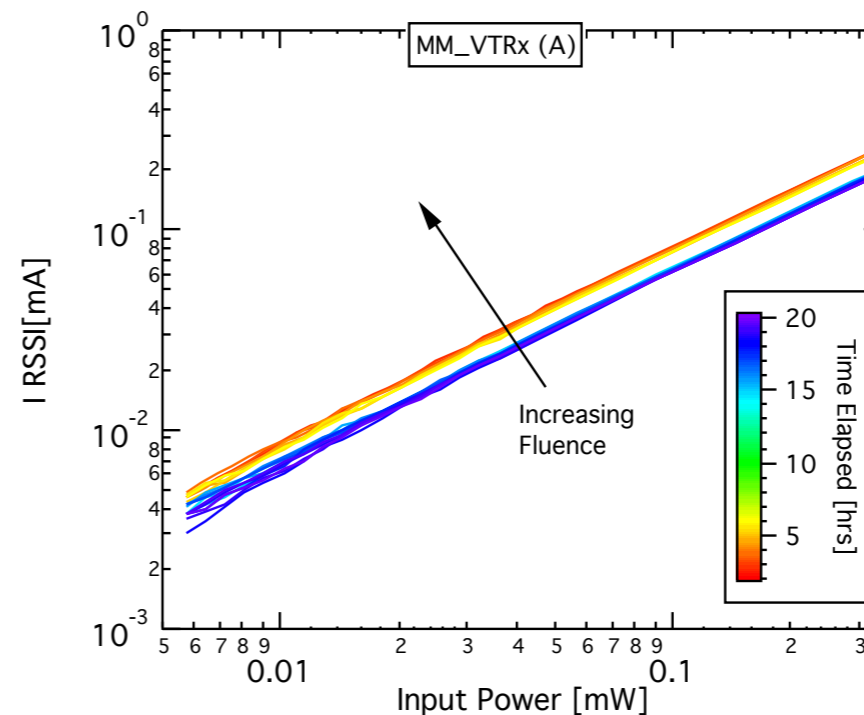
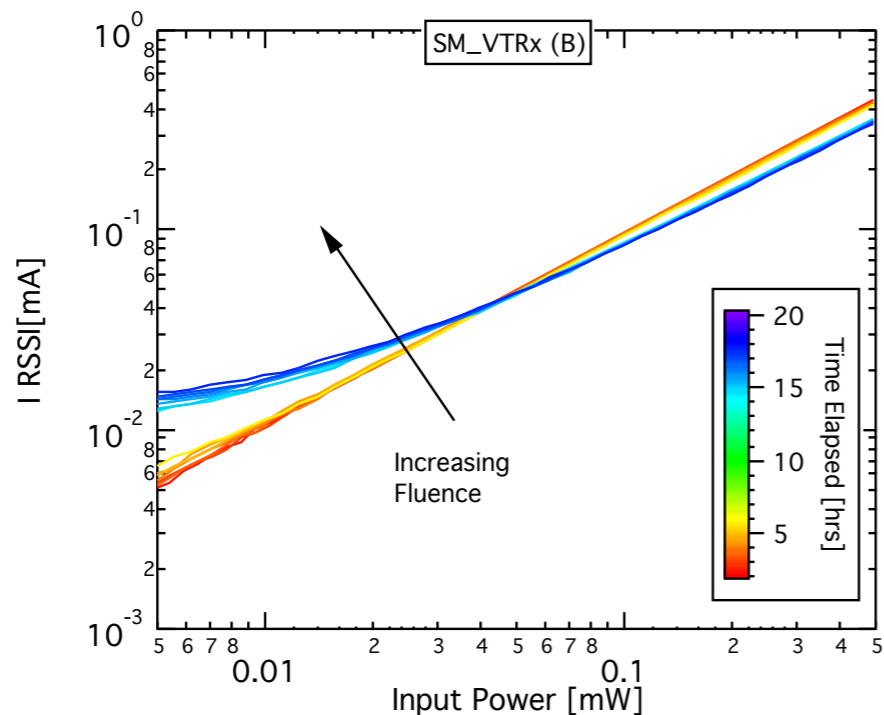
*caused by change in responsivity?*

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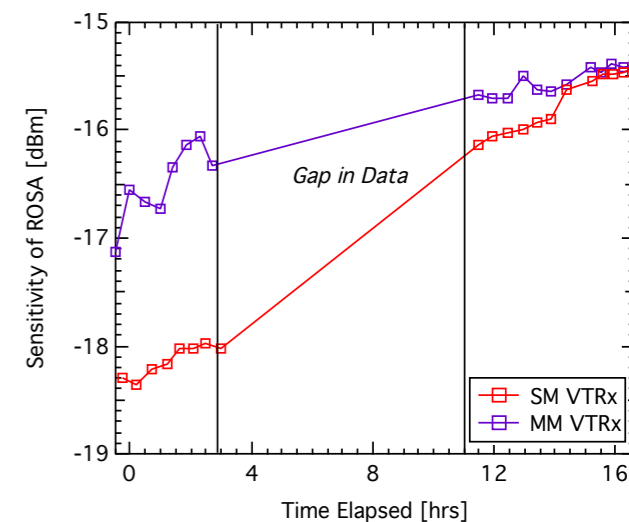
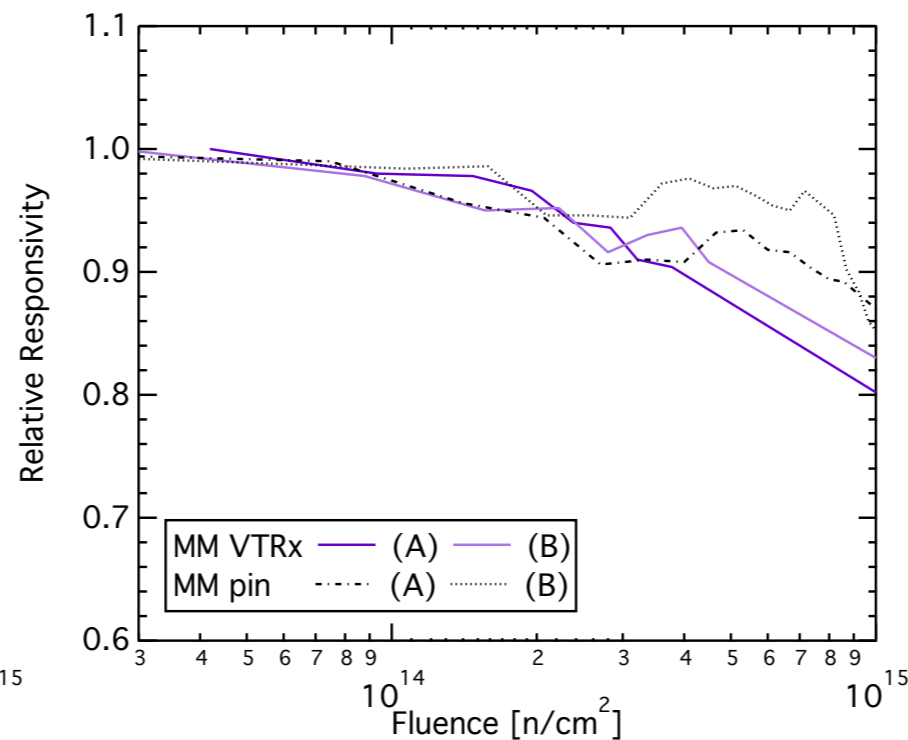
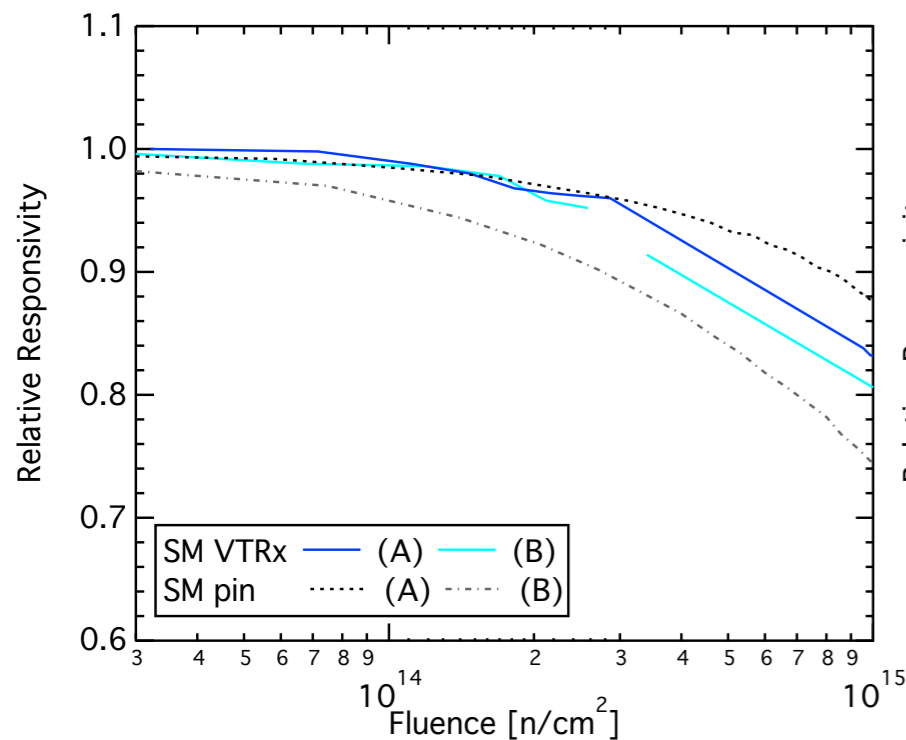
*caused by change in responsivity?*

- RSSI current measurement used to calculate change of responsivity of ROSAs during irradiation



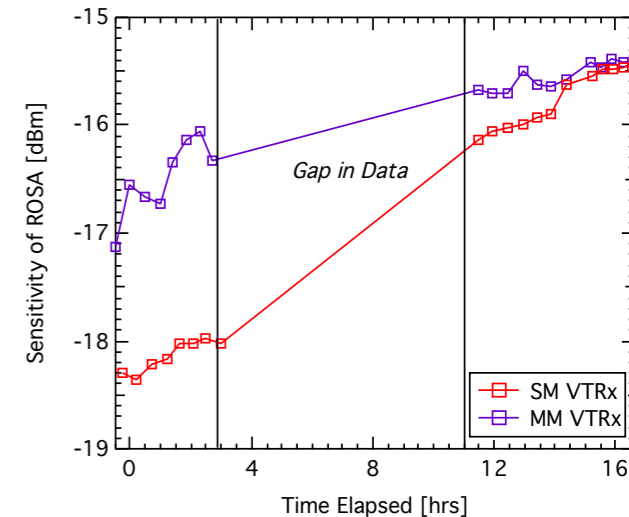
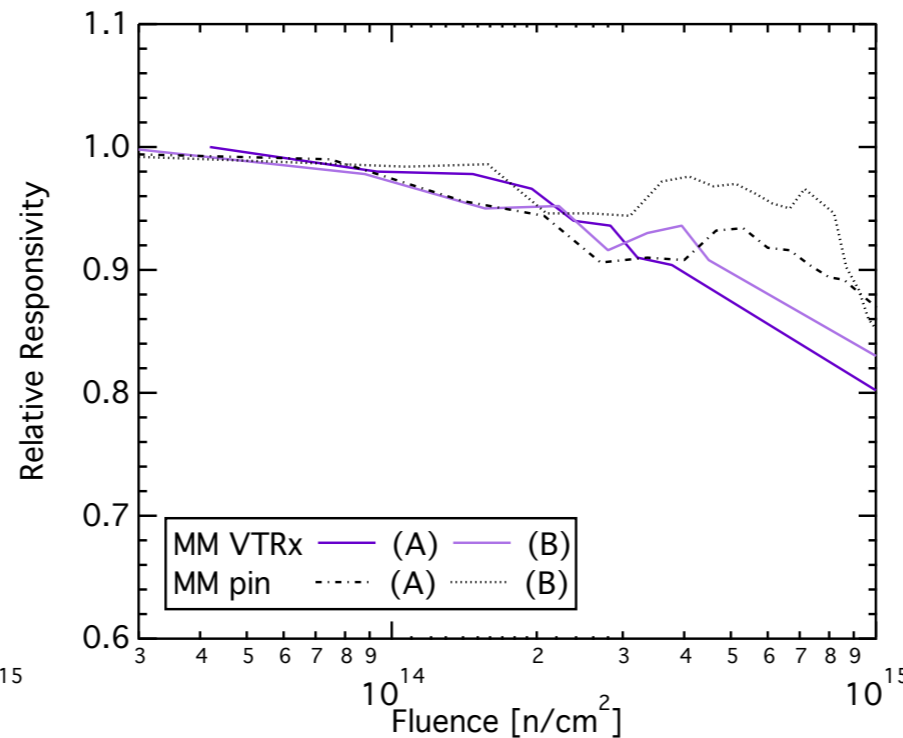
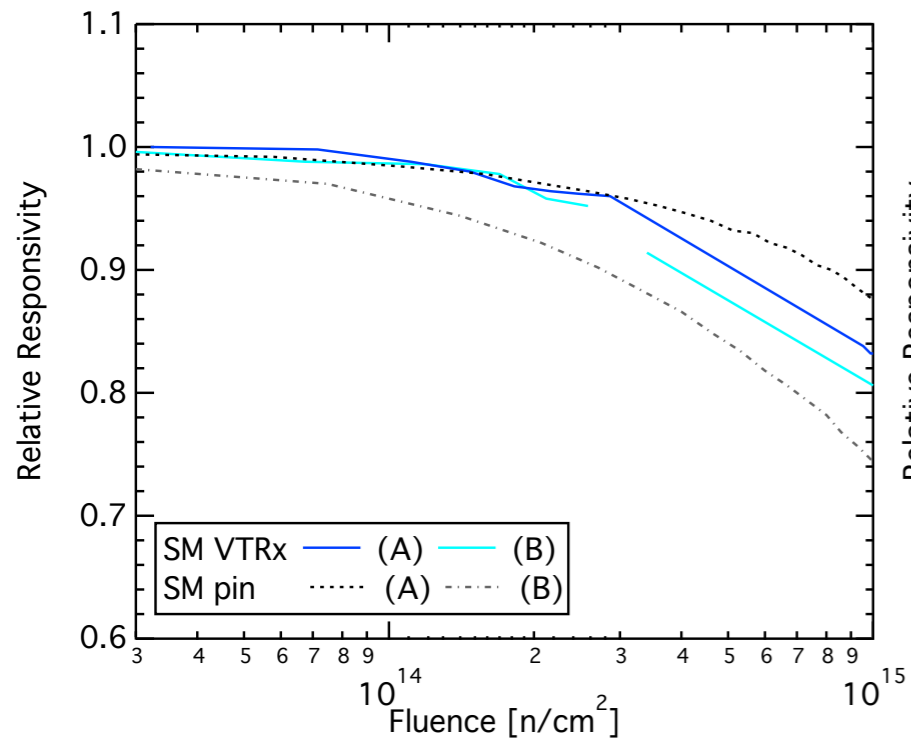


- Change in responsivity of devices comparable with pin photodiodes tested



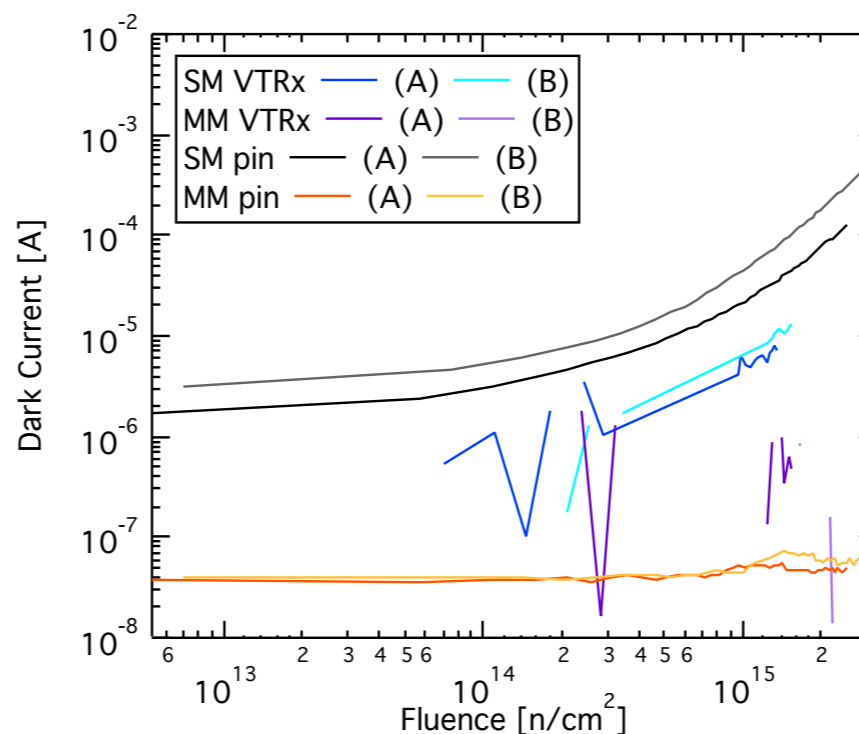
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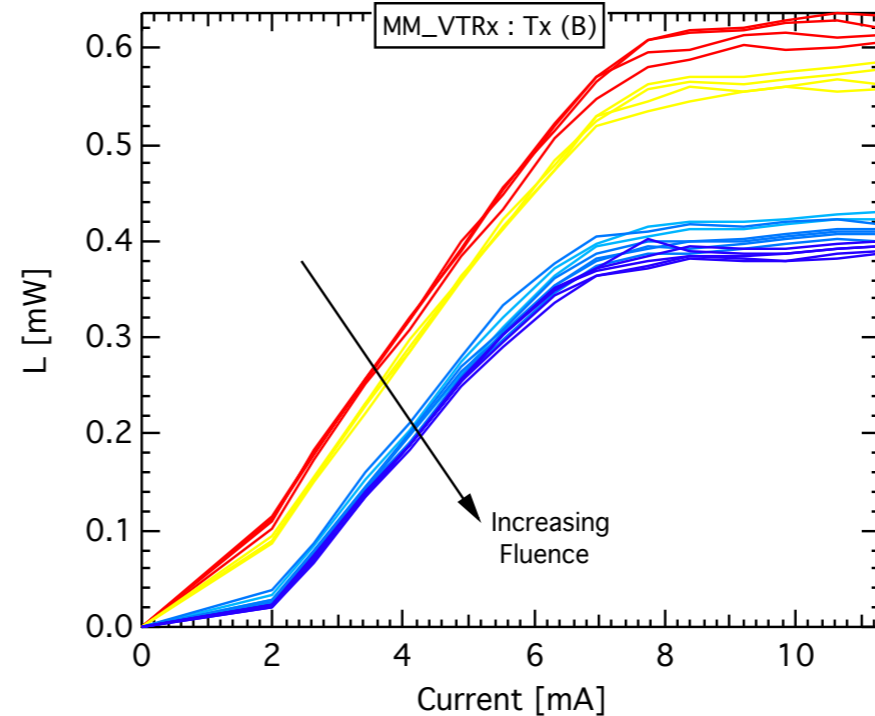
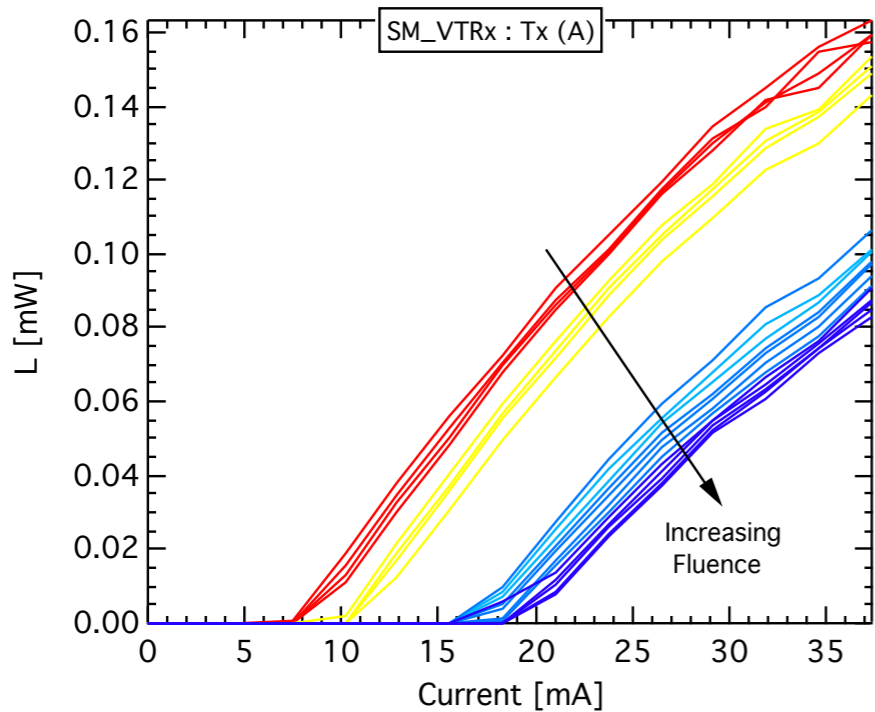


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- Points to change in leakage current being more important than previously thought?

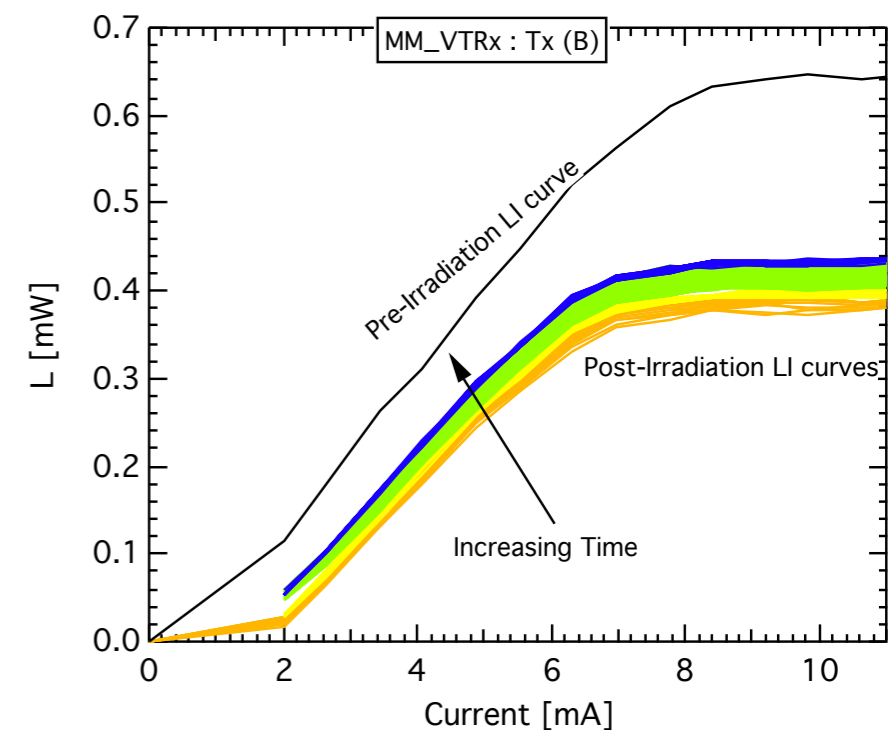
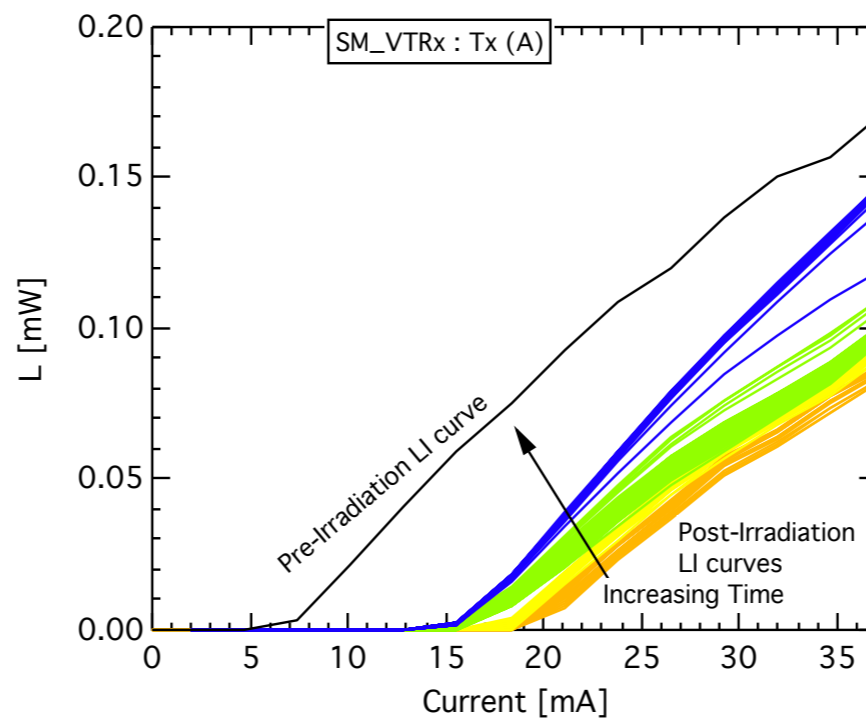


- LI curves of transmitters collected during irradiation
- gap in the data due to problems with set-up during test



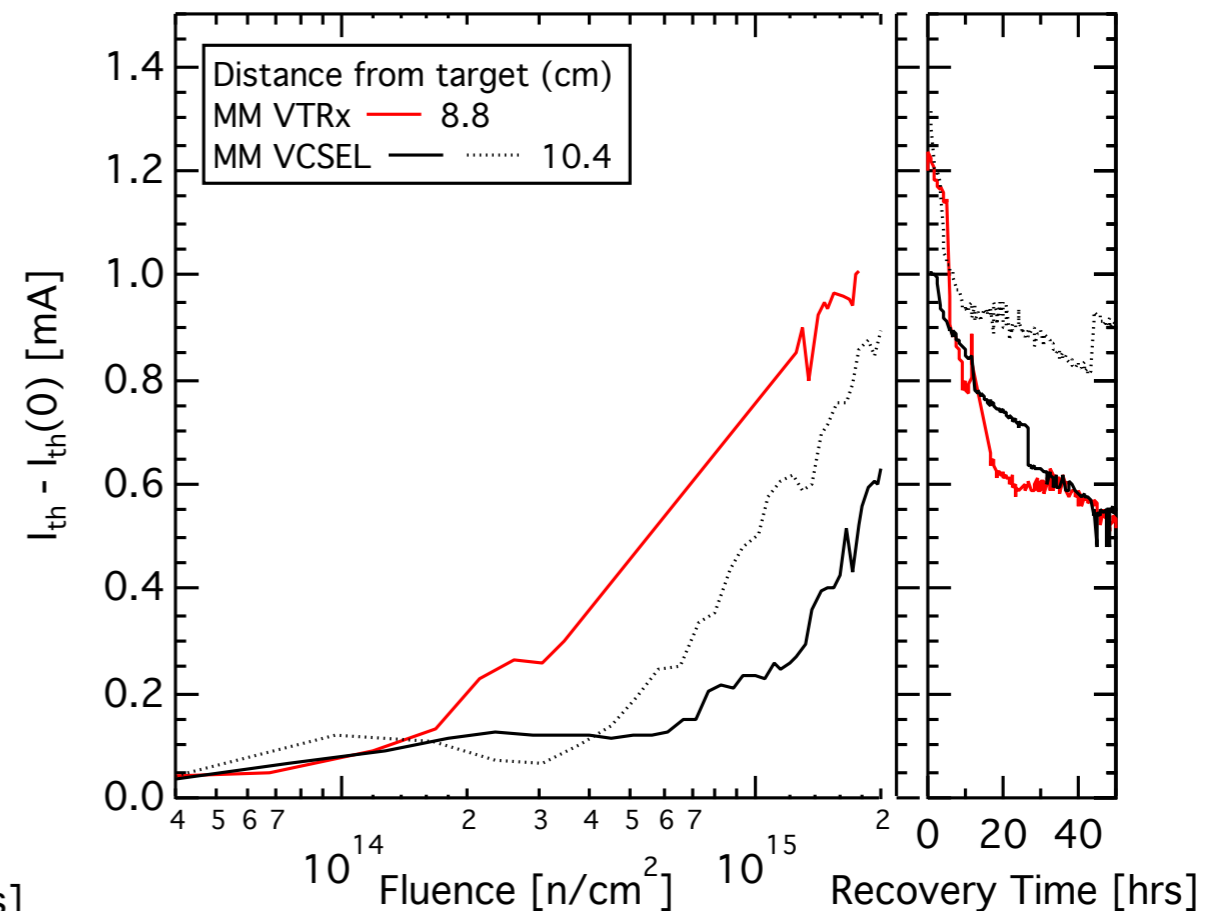
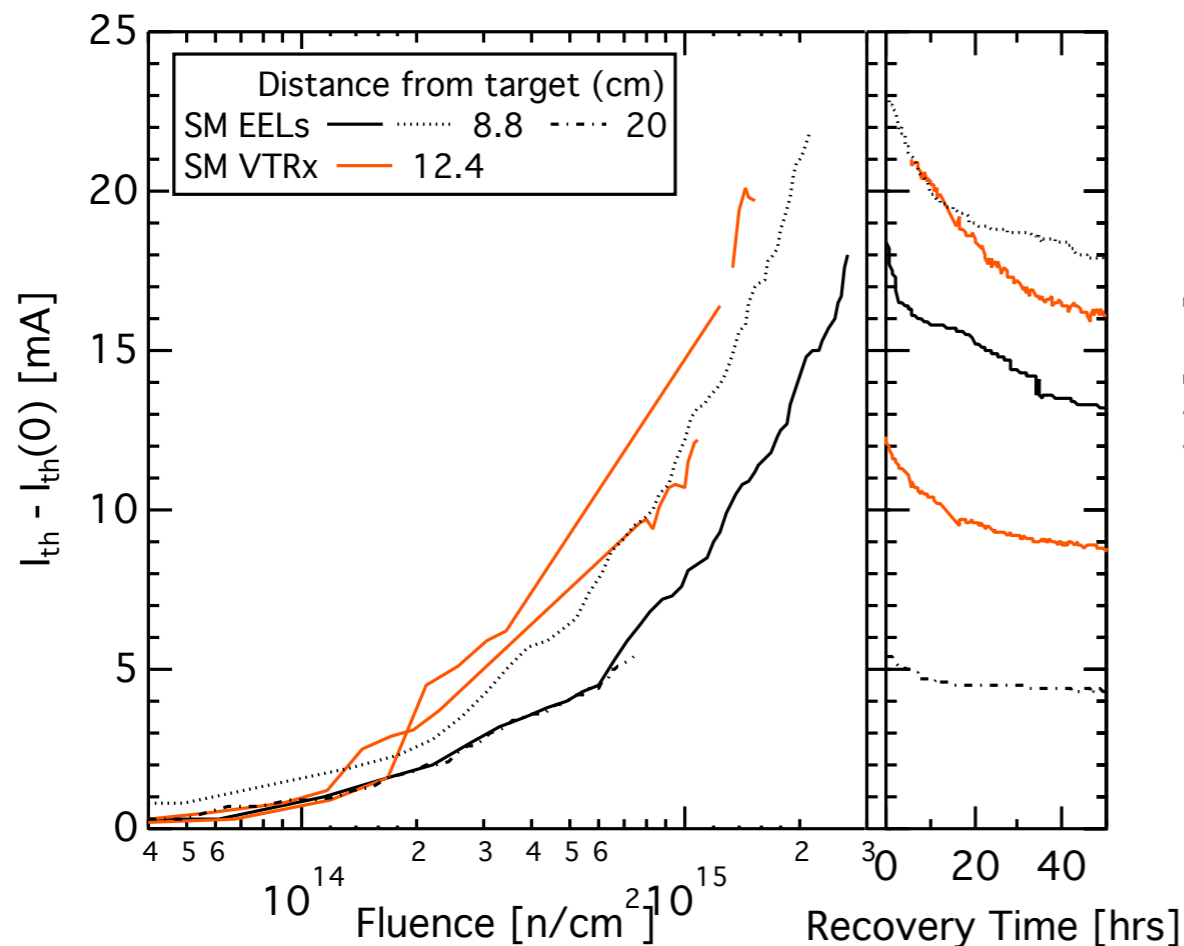
- Expected change in performance of transmitters : increase in threshold current and decrease in slope efficiency

- Fraction of the damage anneals post-irradiation

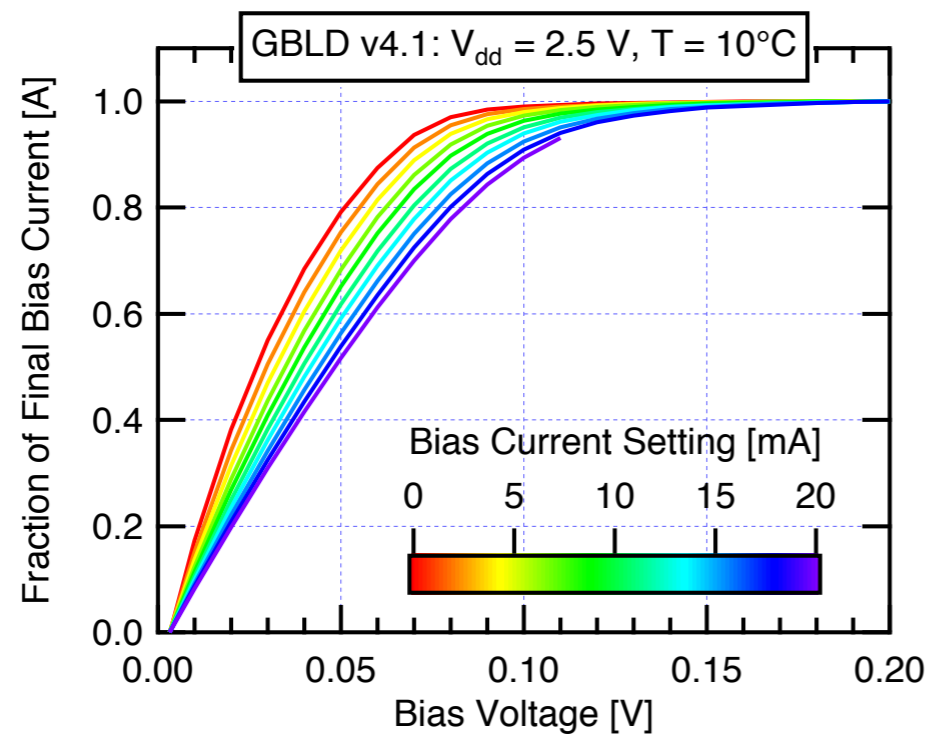


- Are predictions for the expected change in threshold current in VTRx transmitters from irradiations on components measured DC-only of the VTRxs accurate ?
  - transmitters from the same manufactures irradiated in the same test
  - comparison between the change in threshold current in both VTRx and transmitter therefore possible

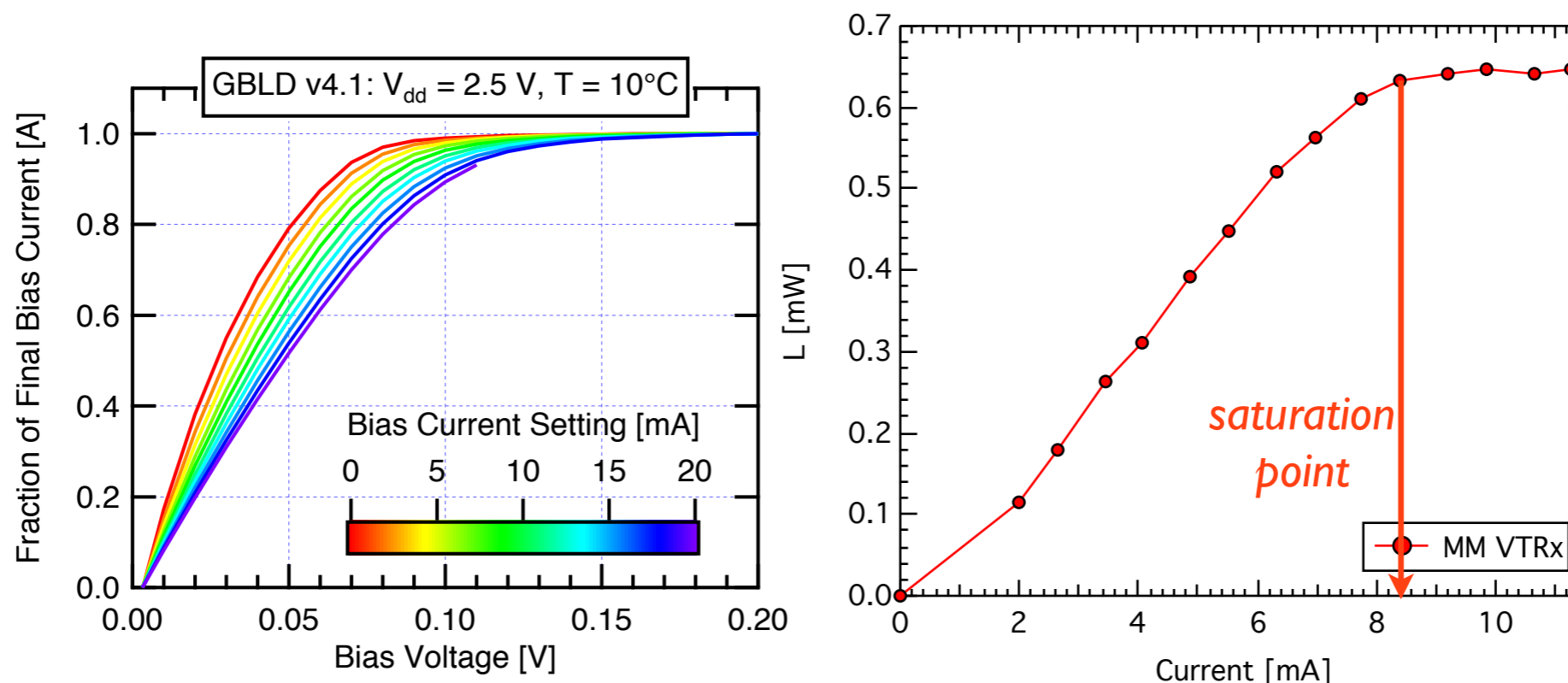
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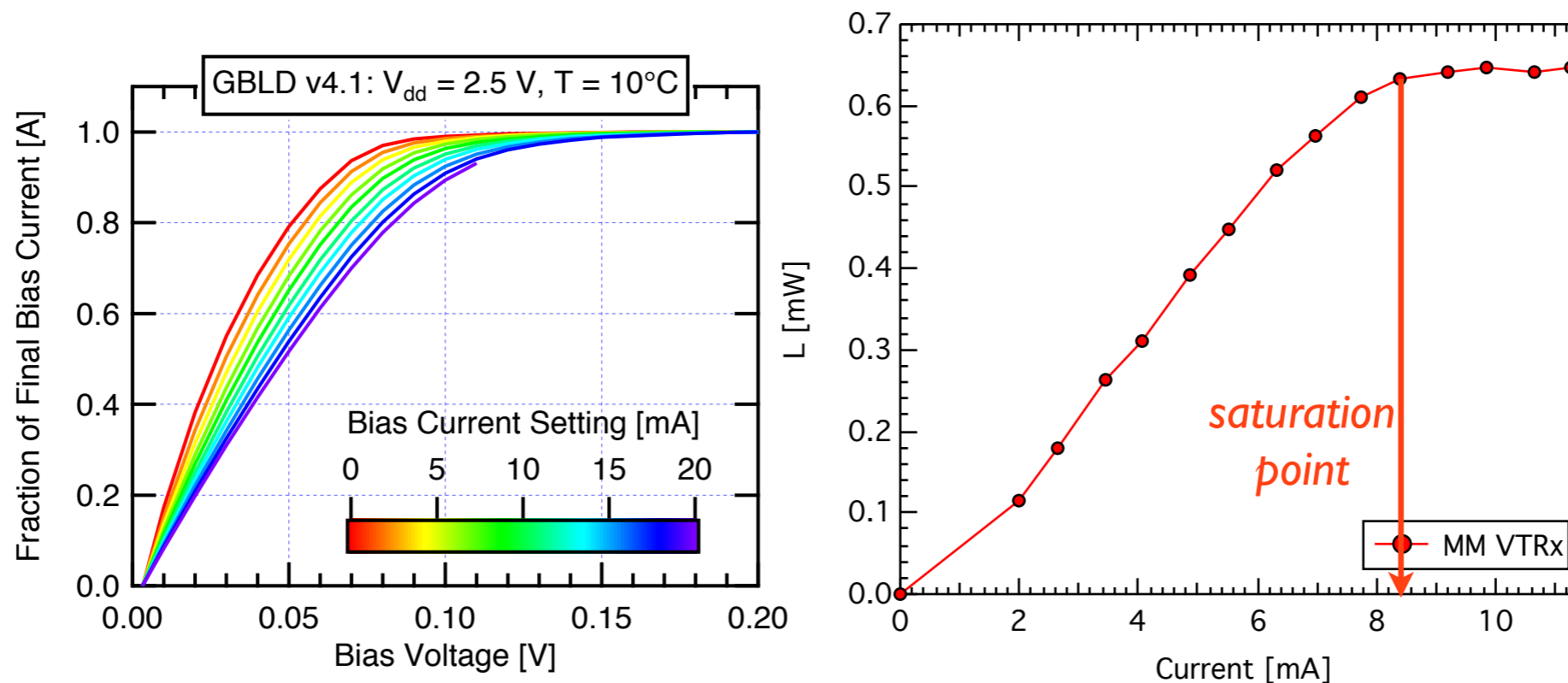
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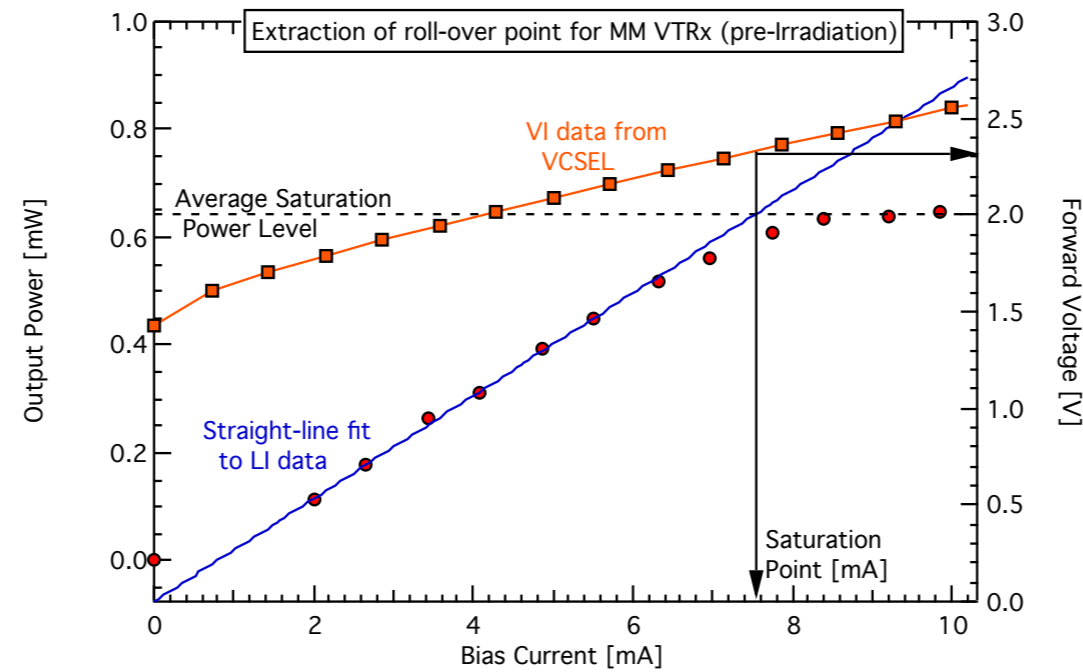
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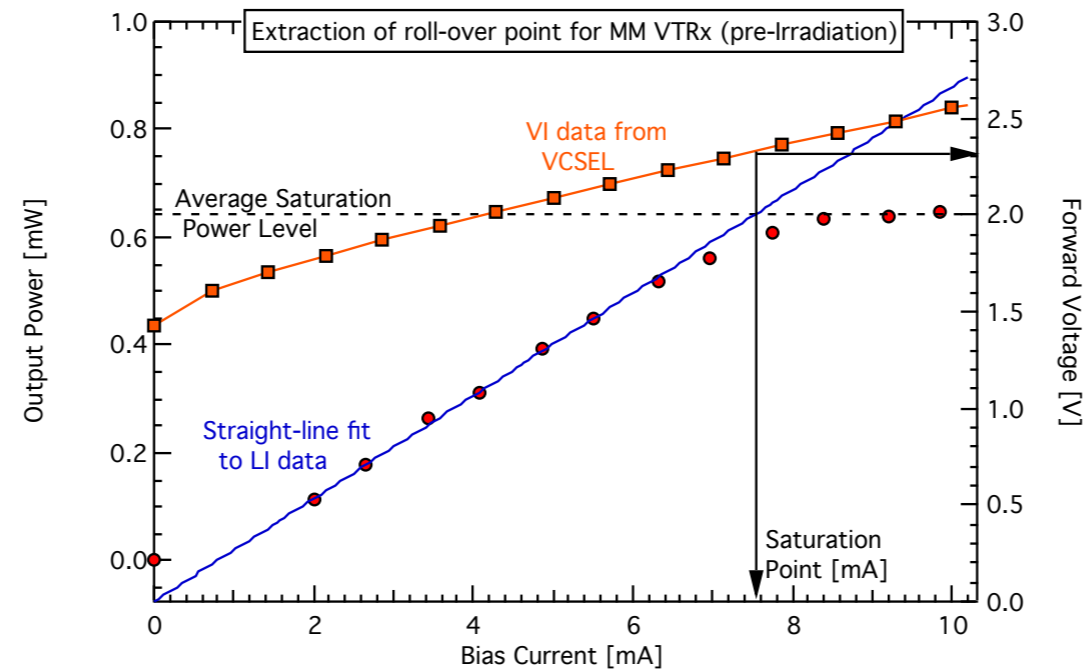
- Expect to see a change in the saturation point of the MM VTR<sub>x</sub> during irradiation
  - can we use the information from the VI curves of irradiated transmitters to predict how the saturation point changes?



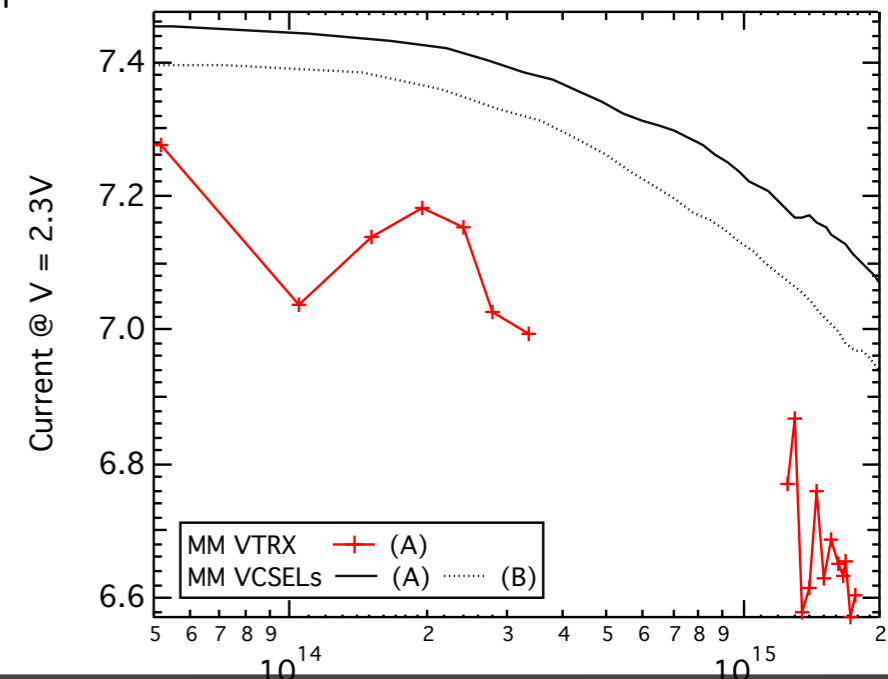
- Voltage at which the GBLD head-room is no longer sufficient extracted from the pre-irradiation data ( $V_{\max}$ )



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- Compare bias current at ( $V_{max}$ ) from VI curves of transmitters to saturation point from LI curves of MM VCSELS during irradiation
  - trends are the same for both devices
  - can use VI data of MM VCSELS to predict change in saturation point of MM VTRxs



- Assumption has always been that the spec for the slope efficiency of the transmitter is such that no additional radiation penalty is required :

- transmitters threshold current and slope efficiency change during irradiation

- OMA depends on both

- can we maintain the minimum OMA during irradiation?

- if not, can we adjust the settings of the VTRx to compensate?

$$OMA = P_1 - P_0 \approx I_{\text{mod}} \eta \Rightarrow \eta = \frac{OMA}{I_{\text{mod}}}$$

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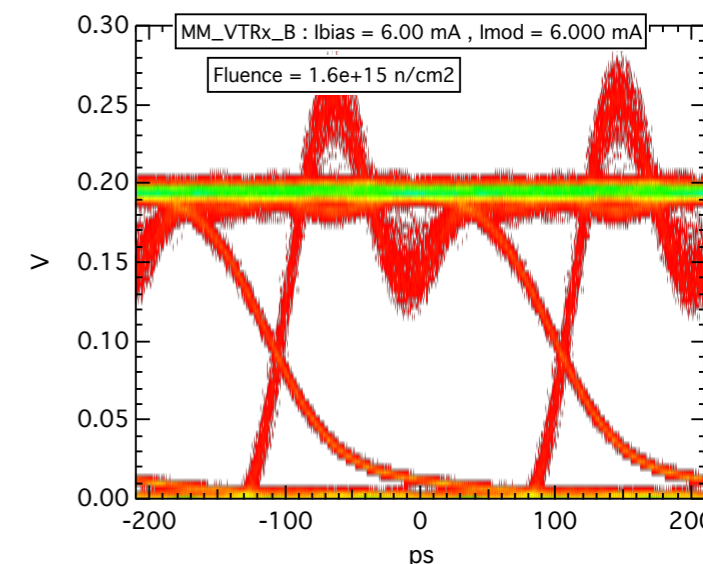
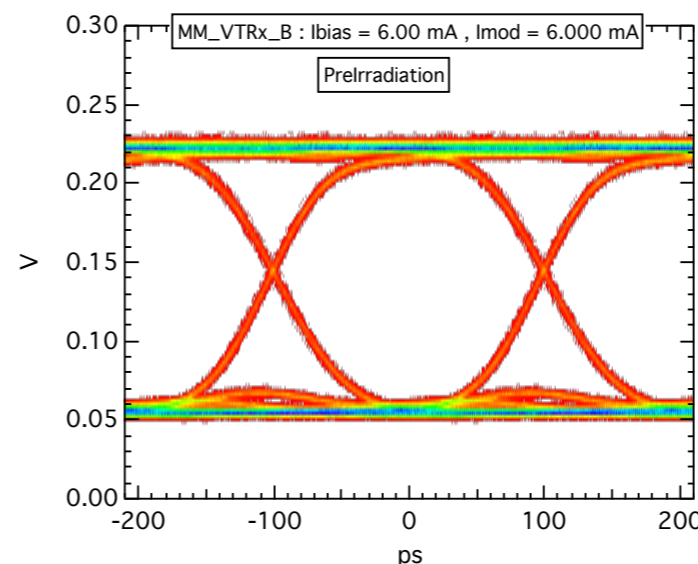
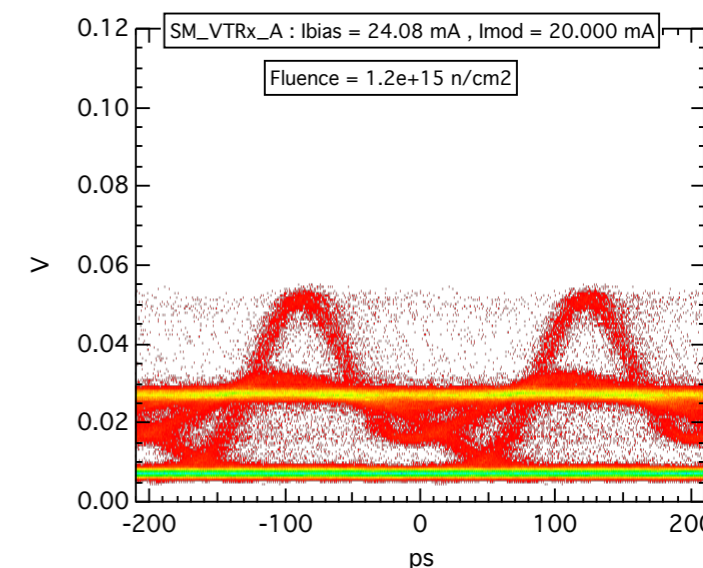
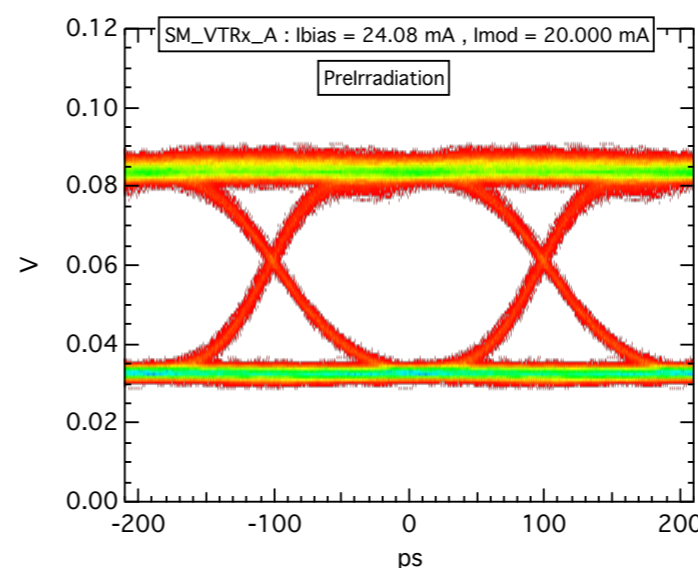
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- Tried to change the transmitter settings (  $I_{mod}$ ,  $I_{bias}$  ) during the test with information obtain from the LI curves to maintain a “good” eye

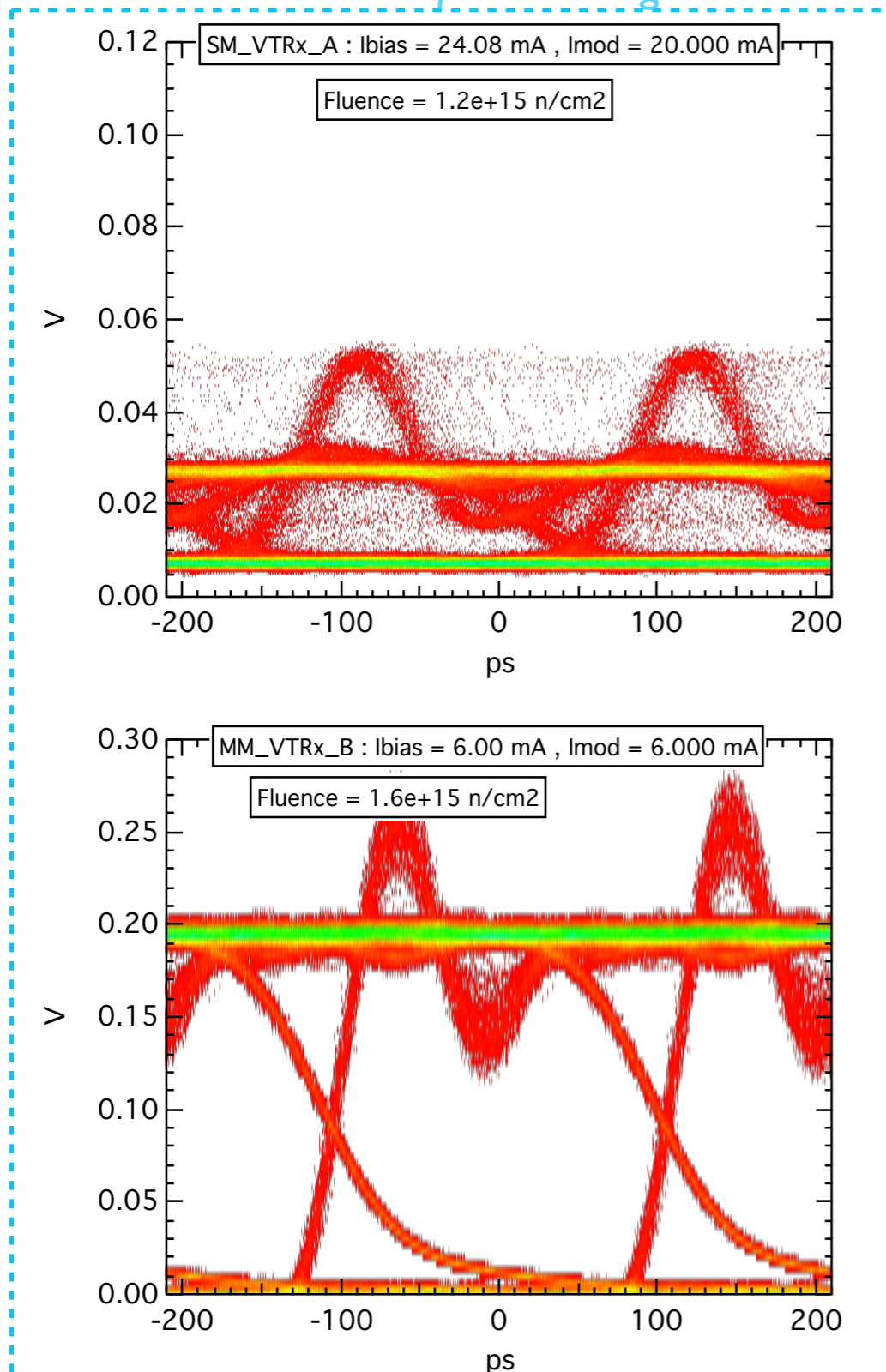
- if we do nothing (i.e. default settings )
- worst in SM case than MM case



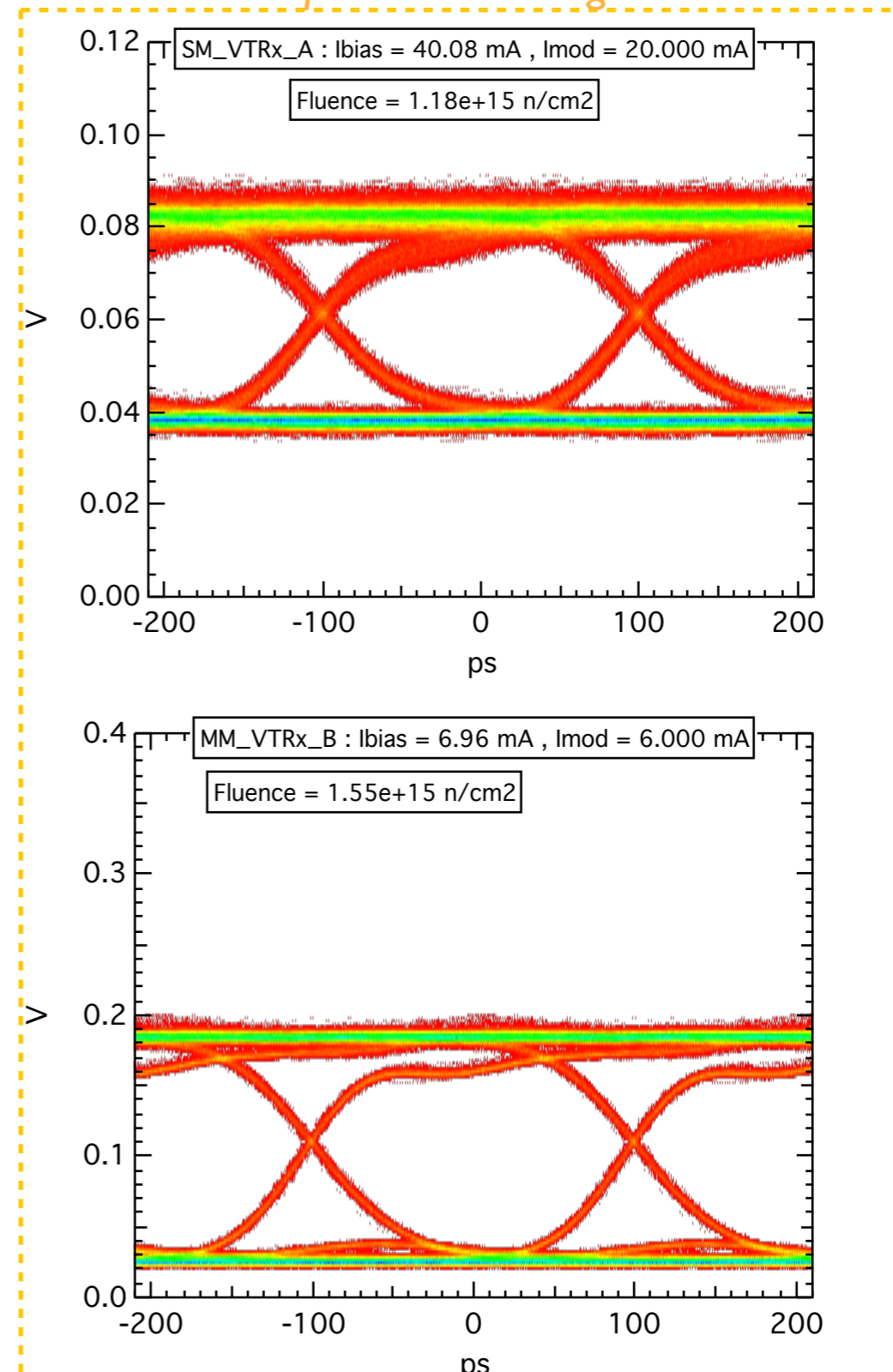
# ► Effect of radiation on transmitter, AC

- Tried to change the transmitter settings ( I<sub>mod</sub>, I<sub>bias</sub> ) during the test with information obtain from the LI curves

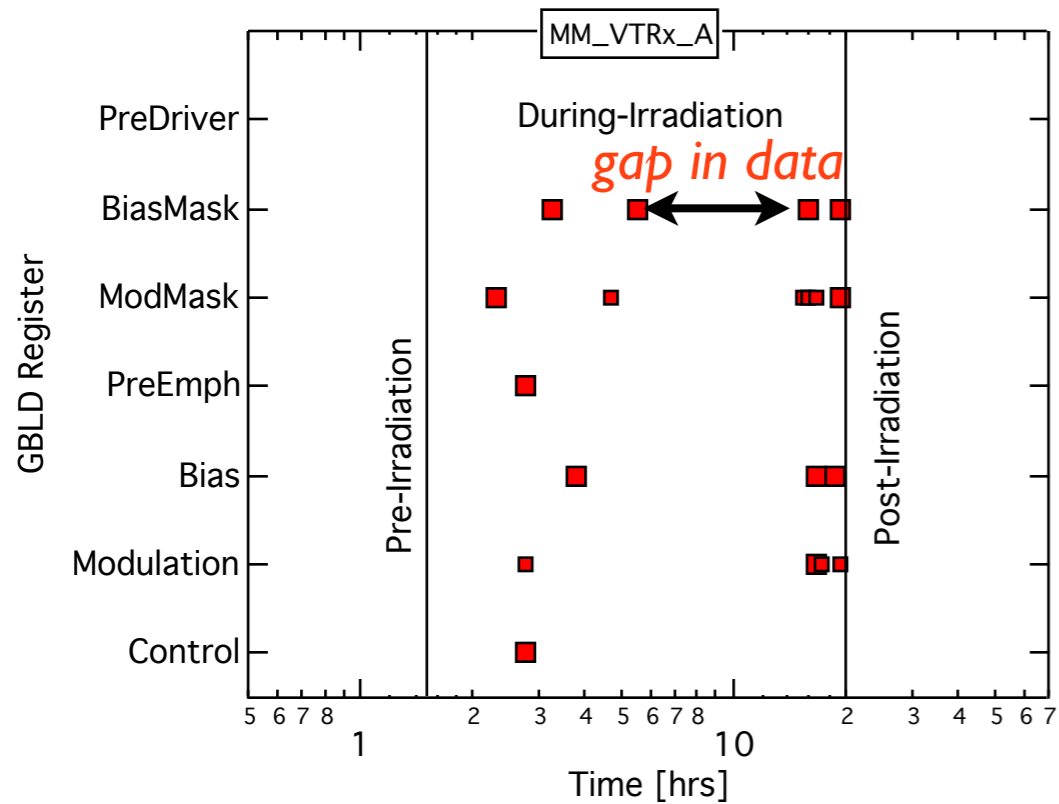
Default Settings



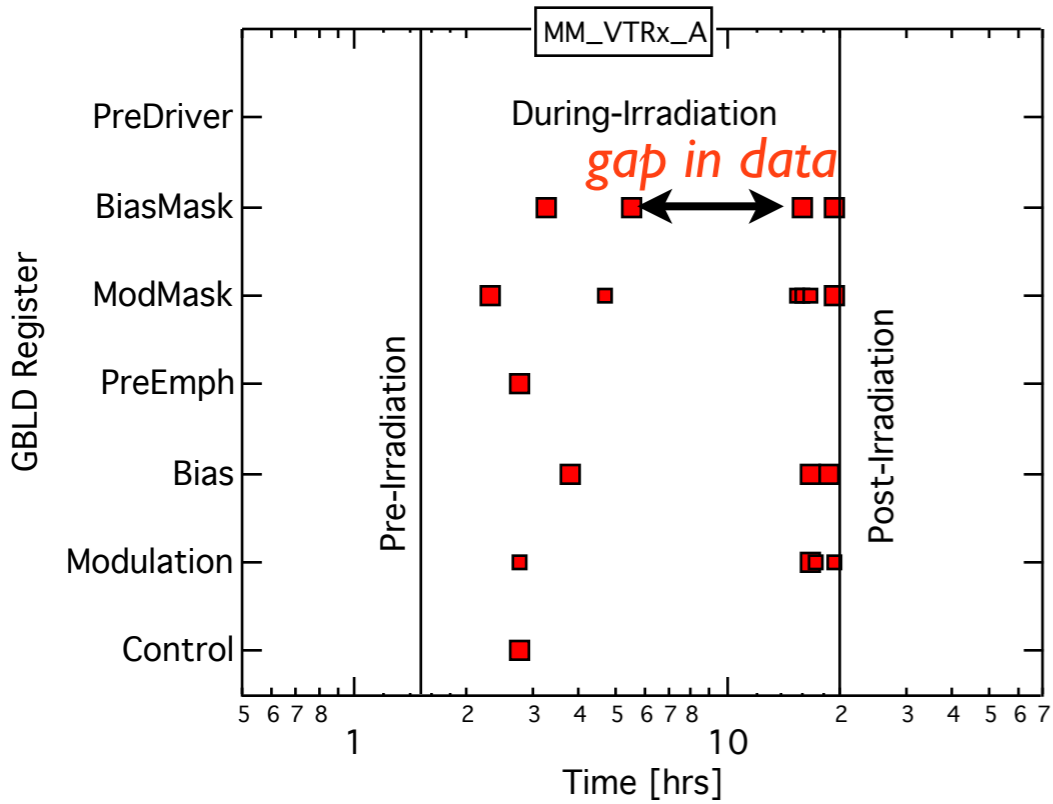
Optimized Settings



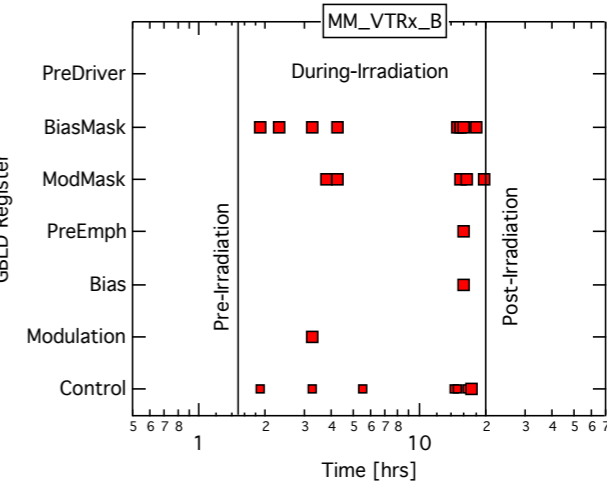
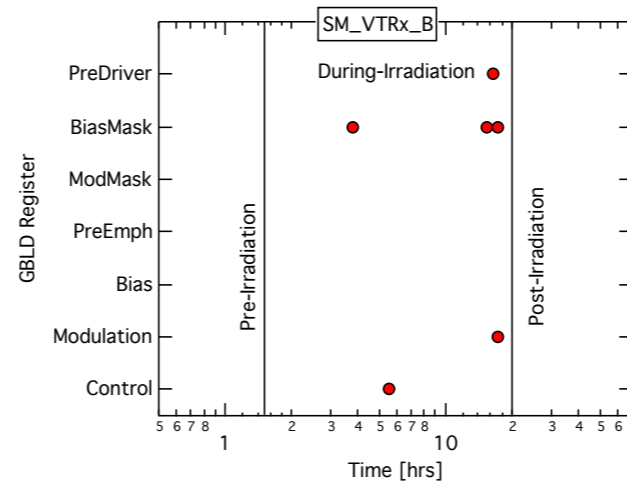
- Checked for SEUs in the GBLD during irradiation
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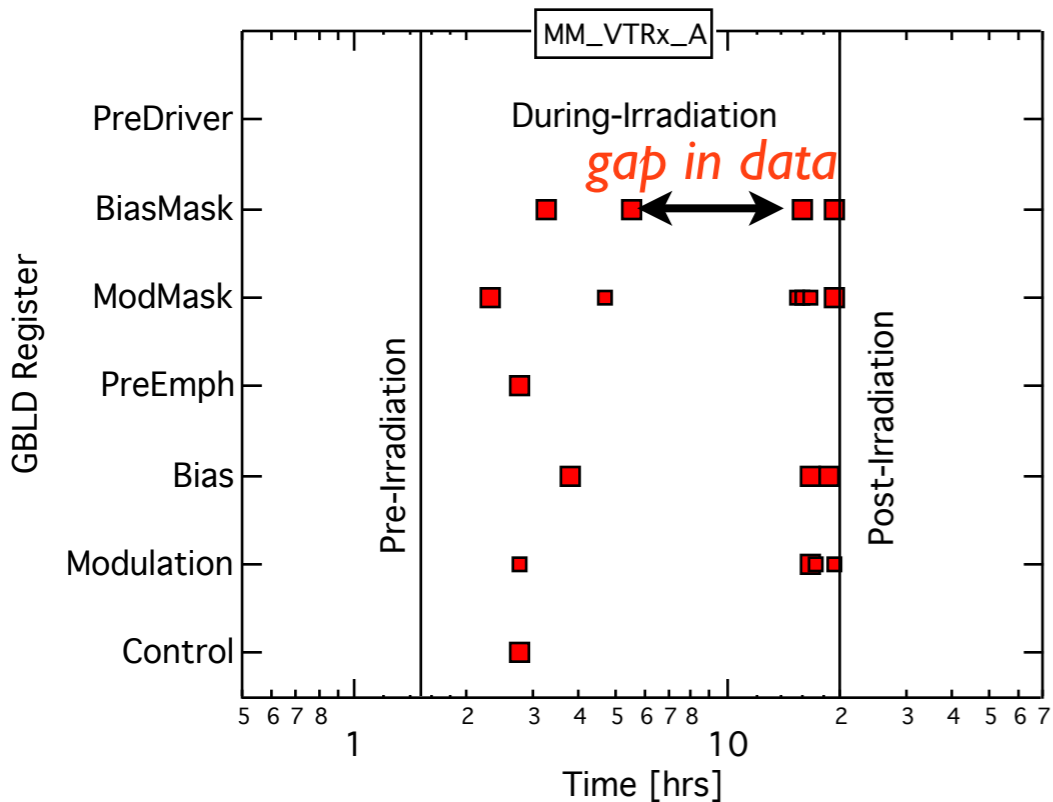


- Clearly see errors in the GBLD during irradiation
- error cross section :  $1.2 \times 10^{-14}$  errors/n/cm<sup>2</sup>
- other devices behaved in a similar manner

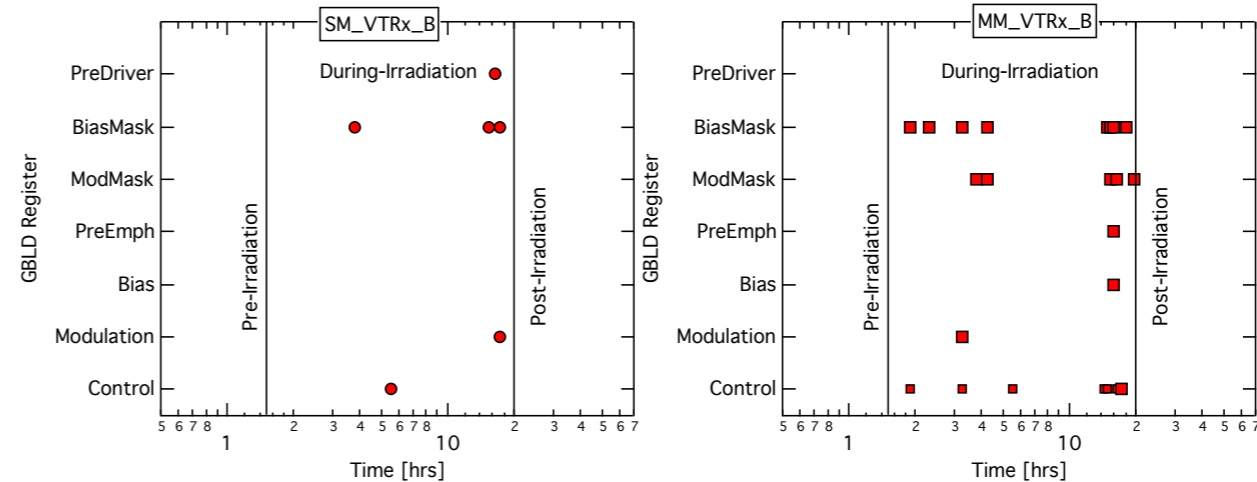


*further away from the beam*

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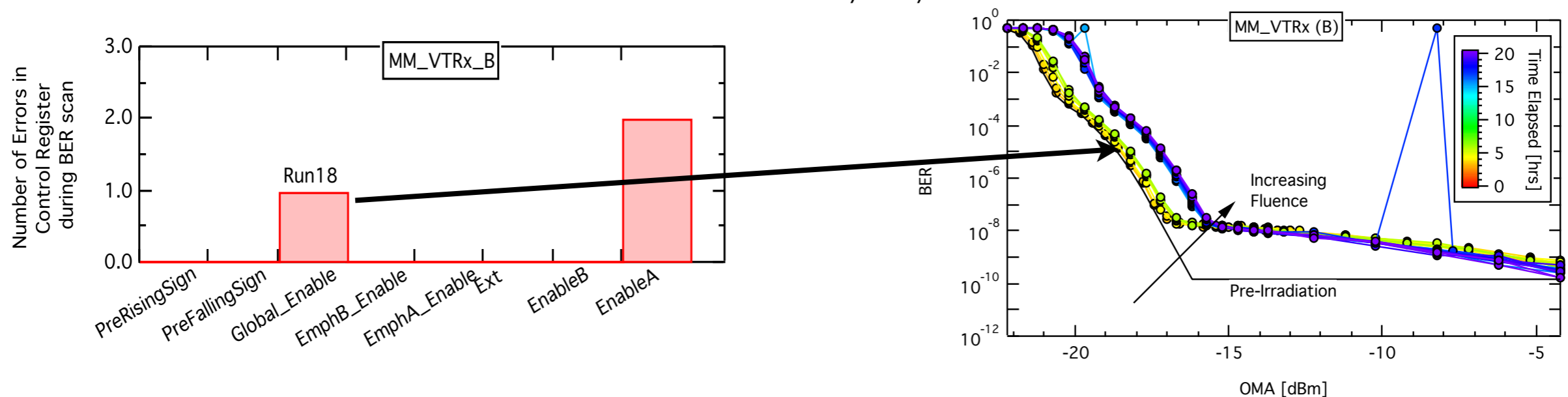


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*further away from the beam*

- Checked whether these errors were “detectable” by any of the on-line measurements we were doing





- **First radiation test on full VTRx object**
  - SM and MM variants with GBLD v4.1 and GBTIA v.2 tested
  - transmitters degrade in the same manner predicted by radiation tests carried out on the passive components
  - change of saturation point of MM VTRxs can be predicted from the change in the VI curves of the transmitters during irradiation
  - leakage current of the photodiodes has a higher than expected impact on the sensitivity of the ROSAs to SEUs
  - SEUs observed in the GBLD
- **Future Plans**
  - Qualification of lasers and photodiodes for production of VTRxs

# Back-Up Slides